

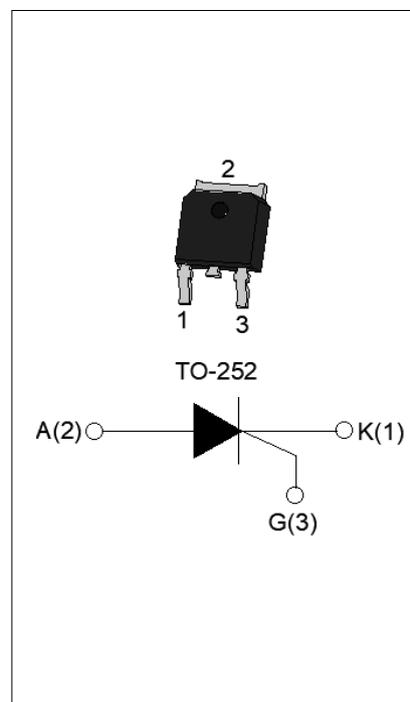


DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1208K provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on hair straightener, motorcycle voltage regulators etc. Package TO-252 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	1200	V
I_{GT}	15	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
Average on-state current ($T_c = 80^\circ\text{C}$)	$I_{T(AV)}$	5	A
RMS on-state current ($T_c = 80^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I_{TSM}	85	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}, T_j=25^\circ\text{C}$)		94	
I^2t value for fusing ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I^2t	36	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100\text{Hz}, T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}, T_j=125^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3K$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	40	mA
I_H	$I_T=500mA$	-	-	30	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$	1000	-	-	V/ μs
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$	-	5	-	μs
t_{off}		-	100	-	μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=16A$ $t_p=380\mu s$	$T_j=25$	1.6	V
V_{TO}	Threshold voltage	$T_j=125$	0.8	V
R_D	Dynamic resistance	$T_j=125$	28	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	10	μA
I_{RRM}		$T_j=125$	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	4.5	/W
$R_{th(j-a)}$	junction to ambient (DC)	120	/W

JCT1208K

 **JieJie Microelectronics Co., Ltd.**

ORDERING INFORMATION

J CT 12 08 K -/
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12:VDRM /VRRM 1200V

FIG.1 Maximum power dissipation versus RMS on-state current

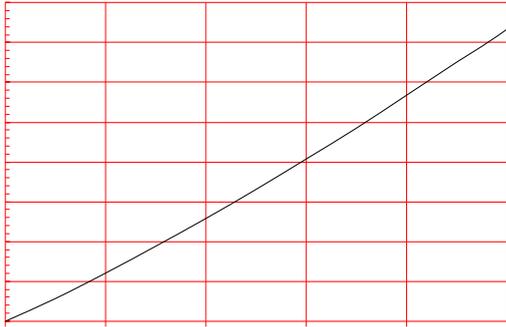


FIG.2: RMS on-state current versus case temperature

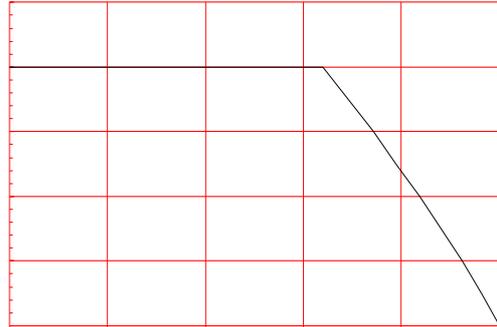


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35 μ m)(full cycle)

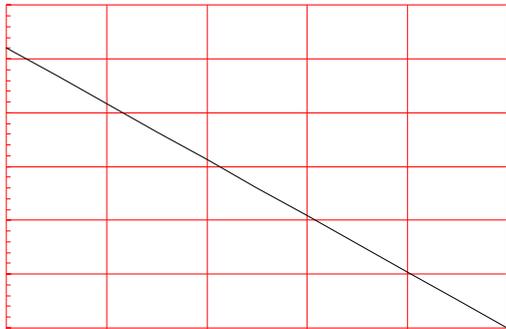


FIG.4: Surge peak on-state current versus number of cycles



FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

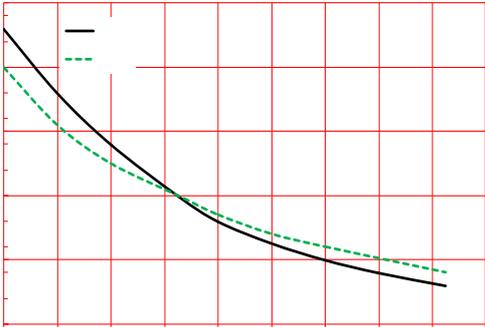
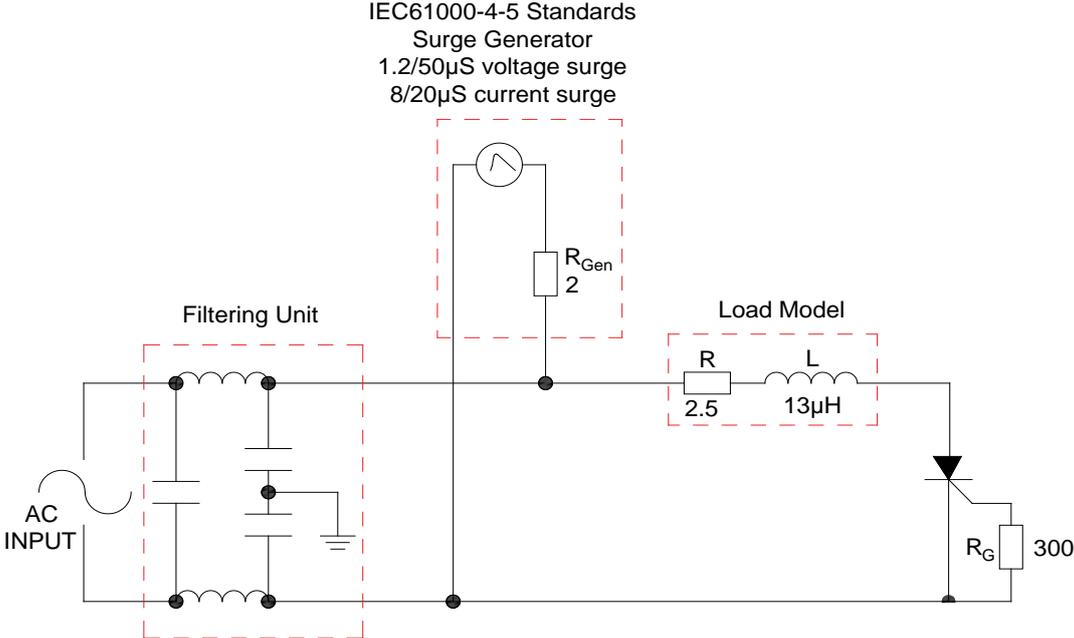
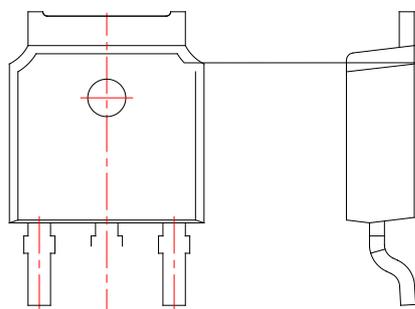


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1						
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

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